

AMENDMENTS TO THE SPECIFICATION

Please amend the paragraph beginning on page 1, line 26 as follows.

However, in consideration of reduction in ~~const~~ cost and in the area occupied by this circuit on an IC chip, the number of the operational amplifiers should be reduced.

Please amend the paragraph beginning on page 2, line 3 as follows.

Japanese patent No. 3-67211 (US patent Ser. No. 4,576,052) discloses another prior art physical quantity detection device satisfying this requirement. Fig. 6 is a schematic circuit diagram of this prior art physical quantity detection device including two operational amplifiers. This prior art physical quantity detection device provides the same function as the physical quantity detection device shown in Fig. 5 with only two operational amplifiers. In the case that the physical quantity detection device is used as a pressure sensor in motor vehicles, it is generally required that the physical quantity detection device is driven by a single power supply of 5 V, so that the output voltage range is from 0.5 to 4.5 V. Moreover, it is further required that the output voltage increases with an increase in presser pressure. Thus, in consideration of these general requirements, the prior art physical quantity detection device shown in Fig. 6 has the following disadvantages.

Please amend the paragraph beginning on page 5, line 17 as follows.

According to the present invention, a first aspect of the present invention provides a physical quantity detection device ~~comprising~~ including: an operational amplifier; a first resistor connected between an inverting input of said the operational amplifier and a first reference potential; a second resistor connected between said the inverting input of said the operational

amplifier and a second reference potential, said the first and second resistors having a first temperature coefficient of resistance; a feedback resistor being connected between said the inverting input of said the operational amplifier and an output of said the operational amplifier and having a second temperature coefficient of resistor resistance; and a reference voltage generation circuit generating a reference voltage supplied to a non-inverting input of said the operational amplifier, at least one of said the first and second resistors comprising including a sensing element of which resistance varying varies on the basis of a physical quantity with a temperature coefficient of sensitivity, wherein a difference between said the first temperature coefficient of resistance and said the temperature coefficient of sensitivity being is substantially equal to said the second temperature coefficient of resistance.

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Please amend the paragraph beginning on page 6, line 10 as follows.

According to the present invention, a second aspect of the present invention provides the physical quantity detection device based on the first aspect, wherein each of said the first and second resistors and said the feedback resistor comprises includes a diffused resistor, and a concentration of impurity of said the feedback resistor is different from concentrations of impurity of said the first and second resistors.

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Please amend the paragraph beginning on page 6, line 16 as follows.

According to the present invention, a third aspect of the present invention provides the physical quantity detection device based on the second aspect, wherein said the concentrations of impurity of said the first and second resistors are from $0.4 \times 10^{19} \text{ cm}^{-3}$ to $8 \times 10^{19} \text{ cm}^{-3}$ and said the concentration of impurity of said the feedback resistor is from $1.6 \times 10^{17} \text{ cm}^{-3}$ to $7 \times$

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10^{17} cm $^{-3}$. Moreover, said the concentrations of impurity of said the first and second resistors may be from 0.8×10^{19} cm $^{-3}$ to 4×10^{19} cm $^{-3}$ and said the concentration of impurity of said the feedback resistor is from 2.5×10^{17} cm $^{-3}$ to 5.5×10^{17} cm $^{-3}$. Furthermore, said the concentrations of impurity of said the first and second resistors may be about 1×10^{19} cm $^{-3}$, and said the concentration of impurity of said the feedback resistor is about 4×10^{17} cm $^{-3}$.

Please amend the paragraph beginning on page 7, line 2 as follows.

According to the present invention, a fourth aspect of the present invention provides the

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physical quantity detection device based on the first aspect, wherein one of said the first and second resistors comprises includes said the sensing element of which resistance varies on the basis of said the physical quantity, and a resistance of the other of said the first and second resistors does not vary with said the physical quantity.

Please amend the paragraph beginning on page 7, line 9 as follows.

According to the present invention, a fifth aspect of the present invention provides the

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physical quantity detection device based on the first aspect, wherein said the reference voltage generation circuit includes third and fourth resistors connected in series between said the first and second reference potentials and generates a divided voltage as said the reference voltage, and a temperature coefficient of resistance of said the third resistor is substantially equal to a temperature coefficient of resistance of said the fourth resistor.

Please amend the paragraph beginning on page 7, line 17 as follows.

According to the present invention, a sixth aspect of the present invention provides the physical quantity detection device based on the fifth aspect, wherein one of said the third and fourth resistors has a trimming structure to trim said the reference voltage toward an output voltage of said the operational amplifier on when said the physical quantity is zero.

Please amend the paragraph beginning on page 7, line 23 as follows.

According to the present invention, a seventh aspect of the present invention provides the physical quantity detection device based on the first aspect, further comprising including a resistor having a trimming structure and that is connected in parallel to said the feedback resistor.

Please amend the paragraph beginning on page 8, line 1 as follows.

According to the present invention, an eighth aspect of the present invention provides the physical quantity detection device based on the first aspect, further comprising including: a third resistor; another operational amplifier having an inverting input supplied with an output of said the operational amplifier through said the third resistor, a non-inverting input of said the another operational amplifier being supplied with said the reference voltage; and a fourth resistor disposed between an output terminal and inverting input of said the another operational amplifier.

Please amend the paragraph beginning on page 8, line 10 as follows.

According to the present invention, a ninth aspect of the present invention provides the physical quantity detection device based on the eighth aspect, further comprising including an

A10 offset trimming resistor between said the first reference potential and said the inverting input of said the another operational amplifier.

Please amend the paragraph beginning on page 8, line 15 as follows.

According to the present invention, a tenth aspect of the present invention provides the physical quantity detection device based on the ~~eight~~ eight aspect, further comprising including an offset trimming resistor between said the second reference potential and said the inverting input of said the another operational amplifier.

Please amend the paragraph beginning on page 8, line 20 as follows.

According to the present invention, an eleventh aspect of the present invention provides the physical quantity detection device based on the eighth aspect, further comprising: including fifth and sixth resistors connected between said the first reference potential and said the inverting input of said the second operational amplifier; and seventh and eighth resistors connected between said the inverting input of said the another operational amplifier and said the second reference potential, wherein said the sixth and seventh resistors have temperature dependencies of resistance.

Please amend the paragraph beginning on page 9, line 3 as follows.

According to the present invention, a twelfth aspect of the present invention provides the physical quantity detection device based on the eleventh aspect, wherein at least one of said the fifth and eighth resistors has a trimming structure for compensating a temperature characteristic of offset of the output of said the another operational amplifier.

Please amend the paragraph beginning on page 9, line 9 as follows.

According to the present invention, a thirteenth aspect of the present invention provides the physical quantity detection device ~~as claimed in claim 1~~, wherein if it is assumed that a sensitivity of ~~said the~~ sensing element at a reference temperature is S0, a resistance of ~~said the~~ sensing element at ~~said the~~ reference temperature is R0, and a resistance of ~~said the~~ feedback resistor at ~~said the~~ reference temperature is Rts0, then, it is represented that ~~said the~~ sensitivity of ~~said the~~ sensing element at a temperature t which is different from ~~said the~~ reference temperature by T is S(T), ~~said the~~ resistance of ~~said the~~ sensing element at t is R(T), and ~~said the~~ resistance of ~~said the~~ feedback resistor at t is Rts(T), and S(T), R(T), and Rts(T) are further represented by:
$$S(T) = S0 \cdot (1 + \beta1 \cdot T + \beta2 \cdot T^2), R(T) = R0 \cdot (1 + \alpha1 \cdot T + \alpha2 \cdot T^2), \text{ and } Rts(T) = Rts0 \cdot (1 + A1 \cdot T + A2 \cdot T^2),$$
 where ~~said~~ $\alpha1, \alpha2, \beta1, \beta2, A1, \text{ and } A2$ are temperature coefficients, and wherein ~~said~~ $\alpha1, \alpha2, \beta1, \beta2, A1, \text{ and } A2$ are determined so as to establish both $A1 = \alpha1 - \beta1$ and $A2 = \alpha2 - \beta2 - \beta1 \cdot (\alpha1 - \beta1).$

Please amend the paragraph beginning on page 9, line 25 as follows.

According to the present invention, a fourteenth aspect of the present invention provides the physical quantity detection device based on the first aspect, wherein ~~said the~~ reference voltage is determined such that almost all of a current flowing through ~~said the~~ first resistor flows into ~~said the~~ second resistor.

Please amend the paragraph beginning on page 10, line 4 as follows.

According to the present invention, a fifteenth aspect of the present invention provides a physical quantity detection device comprising including: an operational amplifier; a first resistor connected between an inverting input of said the operational amplifier and a first reference potential; a second resistor connected between said the inverting input of said the operational amplifier and a second reference potential, said the first and second resistors having a first temperature coefficient of resistance; a feedback resistor being connected between said the inverting input of said the operational amplifier and an output of said the operational amplifier and having a second temperature coefficient of resistor resistance; a reference voltage generation circuit generating a reference voltage supplied to a non-inverting input of said the operational amplifier, at least one of said the first and second resistors comprising including a sensing element of which resistance varying varies on the basis of a physical quantity with a temperature coefficient of sensitivity, wherein said the reference voltage generation circuit includes a third resistor and a fourth resistor connected in series between said the first and second reference potentials and generates a divided voltage as said the reference voltage, and a temperature coefficient of said the third resistor is substantially equal to a temperature coefficient of said the fourth resistor.

Please amend the paragraph beginning on page 10, line 25 as follows.

According to the present invention, a sixteenth aspect of the present invention provides a physical quantity detection device comprising including: an operational amplifier; a first resistor connected between an inverting input of said the operational amplifier and a first reference potential; a second resistor connected between said the inverting input of said the operational

amplifier and a second reference potential, said the first and second resistors having a first temperature coefficient of resistance; a feedback resistor being connected between said the inverting input of said the operational amplifier and an output of said the operational amplifier and having a second temperature coefficient of ~~resistor~~ resistance; a reference voltage generation circuit generating a reference voltage supplied to a non-inverting input of said the operational amplifier, at least one of said the first and second resistors comprising including a sensing element of which resistance varying varies on the basis of a physical quantity with a temperature coefficient of sensitivity, a third resistor; another operational amplifier, an inverting input of said the another operational amplifier being supplied with an output of said the operational amplifier through said the third resistor, a non-inverting input of said the another operational amplifier being supplied with said the reference voltage; and a fourth resistor disposed between an output terminal and the inverting input of said the another operational ~~amplifier~~ amplifier.

Please amend the paragraph beginning on page 14, line 19 as follows.

Generally, if a ~~Wheatstone bridge~~ Wheatstone bridge is constructed with strain gages, the zero point deviates due to slight desperations among four diffused resistors such as dispersion in line width of diffused resistors, so that an offset voltage appears. Thus, conventionally offset adjustment was necessary before adjustment of pressure sensitivity and was carried out with either of a ~~circuit~~ the circuits shown in Fig. 2A or Fig. 2B.

Please amend the paragraph beginning on page 15, line 4 as follows.

However, the resistors 50 to 53 should be subjected to laser trimming for the above-mentioned adjustment, so that thin film resistors having a temperature coefficient of ~~resistor~~

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resistance of almost zero such as CrSi are used as the resistors 50 to 53. Thus, difference in temperature coefficient of resistor resistance between the strain gages and these resistors occurs.

Then, if its temperature varies, the zero point of the bridge will deviate from the previous point.

That is, the temperature characteristic of the offset should be adjusted independently.

Please amend the paragraph beginning on page 16, line 1 as follows.

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Further, the resistors R1 and R2 are of the same type (have the same TCR). This structure prevents deviation of the zero point because resistors having different TCRs are not directly connected in the bridge structure. In addition, it is prevented that the reference voltage Vref varies with temperature variation. Accordingly, if the offset voltage of the operational amplifier OP1 is negligibly low, and the influence by the temperature characteristic of the offset voltage is also negligible, this structure further provides offset temperature characteristic compensation by the above-mentioned offset adjustment with either of the resistor R2 resistors R1 or R2 at a temperature, such as a room temperature.

Please amend the paragraph beginning on page 17, line 17 as follows.

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In this circuit, the feedback resistor Rts comprises a temperature sensitive element, and its temperature coefficient of resistor resistance TCRts of the feedback resistor Rts is determined as follows:

Please amend the paragraph beginning on page 18, line 4 as follows.

The first term of Eq. (2) is $V_{ref} = V_{cc}/2$, and the second term includes the pressure signal component. Thus, $(V_2 - V_{ref})$ can be regarded as the pressure signal. The second term of Eq.

(2) shows that a gage ratio $\Delta R/R$ decreases with increase in temperature. On the basis of this fact, the condition for temperature compensation for the output voltage V_2 is determined by substituting the partial differentiation of the output voltage V_2 with respective to temperature with zero. Then, Eq. (3) is established regarding the temperature coefficient of ~~resistor~~ resistance TCR_{ts} of the feedback resistor R_{ts} as follows:

$$\text{TCR}_{ts} = \text{TCR} - \text{TCS} \quad (3)$$

where TCR is a temperature coefficient of resistance of diffused resistors R_a and R_b, and TCS is a temperature coefficient of sensitivity of the diffused resistors R_a and R_b. Moreover, the temperature coefficient of ~~resistor~~ resistance TCR_{ts} of the feedback resistor R_{ts}, the temperature coefficient of ~~resistor~~ resistance TCR of the diffused resistors R_a and R_b, and the temperature coefficient of sensitivity TCS are ~~represent~~ represented by:

Please amend the paragraph beginning on page 19, line 2 as follows.

During obtaining of Eq. (3), $(\Delta R/R)^2$ is neglected because $\Delta R/R = 0.002$ to 0.02 , i.e., $(\Delta R/R)^2 \ll 1$. From the above-mentioned relations, it is found that if the temperature coefficient of ~~resistor~~ resistance TCR of the feedback resistor R_{ts} satisfies Eq. (3), the temperature characteristic of sensitivity can be compensated.

Please amend the paragraph beginning on page 27, line 15 as follows.

These equations are simultaneous equations, wherein respective left sides are represented by coefficients of ~~resistor~~ resistance R_{ts} and the right sides are represented by coefficients of ~~resistors~~ resistance R_a and R_b.

Please amend the paragraph beginning on page 31, line 5 as follows.

In the above-mentioned embodiments, both diffused resistors Ra and Rb comprise strain gages. However, another pressure sensor can be provided. This pressure sensor includes the diffused resistor Ra as the strain gage and the resistor Rb which may be formed as a resistor other than the strain gage having the same temperature coefficient of ~~resistor~~ resistance TCR as that of the diffused resistor Ra. More specifically, for example, only the diffused resistor Ra is formed in the diaphragm, and the diffused resistor Rb is formed at a place other than the diaphragm 10.

Please amend the abstract of the disclosure beginning on page 41, line 5 as follows.

First and second resistors (sensing elements) are connected in series between first and second potentials. The junction point voltage between the first and second resistor is supplied to an inverting input of a first operational amplifier. The non-inverting input is supplied with a reference voltage Vref generated by third and fourth resistors. A feedback resistor is connected between output and inverting input of the operational amplifier OP1. The difference between a temperature coefficient of ~~resistor~~ resistance TCR of the sensing elements and a temperature coefficient of sensitivity TCS is equalized to a temperature coefficient of ~~resistor~~ resistance of the feedback resistor. Further, the reference voltage is unchanged in accordance with the detected physical quantity or temperature variation.